

DESCRIPTION

The 2SC2712 is available in SOT-23 package

FEATURES

- Low noise: NF=1dB(Typ.), 10dB(Max.)
- Complementary to 2SA1162
- High Voltage and high Current
- High hEF linearity
- Available in SOT-23 package

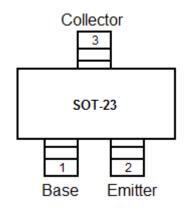
ORDERING INFORMATION

Package Type	Part Number			
SOT-23	2SC2712O			
	2SC2712Y			
	2SC2712G			
	2SC2712L			
Note	SPQ: 3,000pcs/Reel			
AiT provides all RoHS Compliant Products				

APPLICATIONS

 Audio frequency general purpose amplifier applications.

PIN DESCRIPTION





ABSOLUTE MAXIMUM RATINGS

V _{CBO} , Collector-Base Voltage(I _E =0)	60V
V _{CEO} , Collector-Emitter Voltage(I _B =0)	50V
V _{EBO} , Emitter-Base Voltage(I _C =0)	5V
I _C , Collector Current-Continuous	150mA
P _c , Collector Dissipation(T _A =25°C) ^{NOTE1}	150mW
TJ, TSTG, Junction and Storage Temperature	-55°C ~150°C

Stresses above may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated in the Electrical Characteristics are not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

NOTE1: Device is mounted on a printed circuit board.

ELECTRICAL CHARACTERISTICS

T_A=25°C, unless otherwise specified

Parameter	Symbol	Conditions		Min.	Тур.	Max.	Unit
Collector-Base Breakdown Voltage	V _{(BR)CBO}	I _C =100μΑ, I _E =0		60	-	-	V
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	Ic= 0.1mA, I _B =0		50	-	-	V
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	I _E =100µA,I _C =0		5	-	-	V
Collector Cut-off Current	Ісво	V _{CB} =60V, I _E =0		-	-	0.1	uA
Emitter Cut-off Current	I _{EBO}	V _{EB} =5V, I _C =0		-	-	0.1	uA
DC Current Gain	hfe	V _{CE} =6V, I _C =2mA	0	70	-	140	
			Y	120	-	240	
			G	200	-	400	
			L	350	-	700	
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C =100mA, I _B =10mA		-	0.1	0.25	V
Transition Frequency	f⊤	V _{CE} =10V, I _C =1mA		80	-	-	MHz
Output Capacitance	Cob	V _{CB} =10V, I _E =0, f=1kHz		-	2.0	3.5	pF
Noise Figure	NF	V _{CE} =6V, I _C =0.1mA, f=1kHz		-	1.0	10	dB



COMMON EMITTER

ELECTRICAL CHARACTERISTICS CURVES

@ $T_A=25^{\circ}C$, unless otherwise specified

Figure 1. Ic - VCE

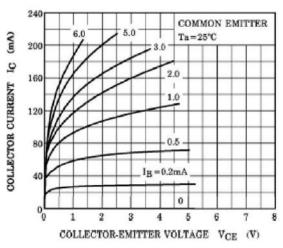


Figure 3. V_{CE(sat)} – I_C

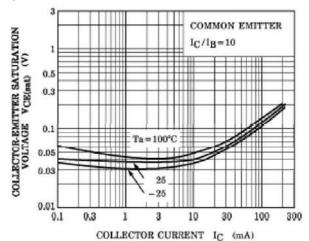
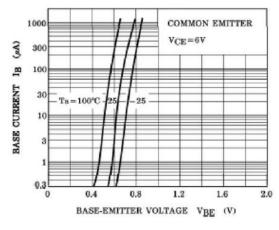


Figure 5. I_B – V_{BE}



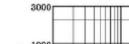
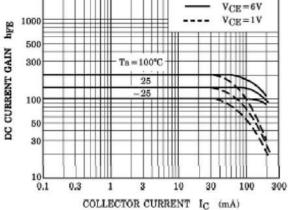


Figure 2. hFE - Ic





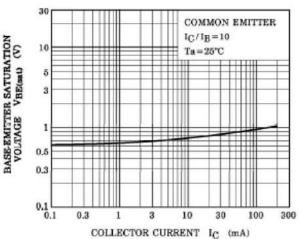
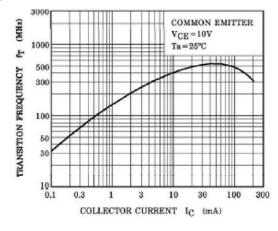


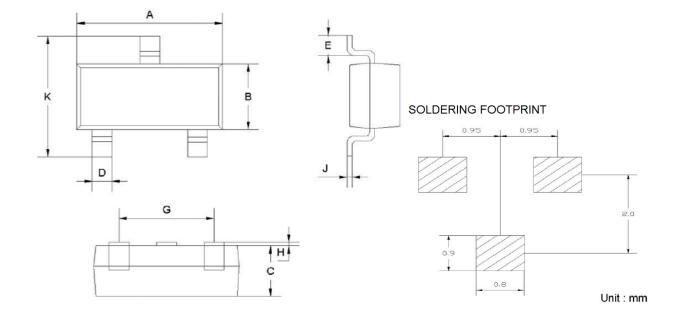
Figure 6. f_T - I_C





PACKAGE INFORMATION

Dimension in SOT-23 (Unit: mm)



Symbol	Min	Max		
А	2.85	2.95		
В	1.25	1.35		
С	1.0 TYP.			
D	0.37	0.43		
E	0.35	0.48		
G	1.85	1.95		
Н	0.02	0.1		
J	0.1 TYP.			
К	2.35 2.45			



IMPORTANT NOTICE

AiT Semiconductor Inc. (AiT) reserves the right to make changes to any its product, specifications, to discontinue any integrated circuit product or service without notice, and advises its customers to obtain the latest version of relevant information to verify, before placing orders, that the information being relied on is current.

AiT Semiconductor Inc.'s integrated circuit products are not designed, intended, authorized, or warranted to be suitable for use in life support applications, devices or systems or other critical applications. Use of AiT products in such applications is understood to be fully at the risk of the customer. As used herein may involve potential risks of death, personal injury, or servere property, or environmental damage. In order to minimize risks associated with the customer's applications, the customer should provide adequate design and operating safeguards.

AiT Semiconductor Inc. assumes to no liability to customer product design or application support. AiT warrants the performance of its products of the specifications applicable at the time of sale.